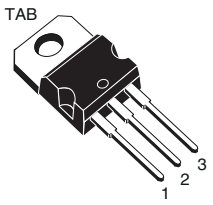
STP180N10F3

N-channel 100 V, 4.5 mΩ, 120 A STripFET™III Power MOSFET TO-220

Features

Order codes	V_{DSS}	$R_{DS(on)}$ max.	I_D
STP180N10F3	100 V	5.1 mΩ	120 A

- Ultra low on-resistance
- 100% avalanche tested



TO-220

Applications

- High current switching applications

Description

This device is an N-channel enhancement mode Power MOSFET produced using STMicroelectronics' STripFET™ III technology, which is specifically designed to minimize on-resistance and gate charge to provide superior switching performance.

Figure 1. Internal schematic diagram

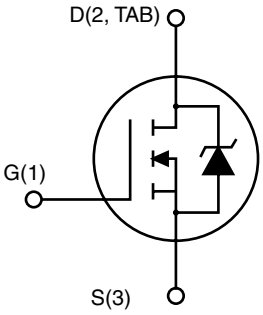


Table 1. Device summary

Order codes	Marking	Package	Packaging
STP180N10F3	180N10F3	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS}=0)	100	V
V_{GS}	Gate-source voltage	± 20	V
I_D (1)	Drain current (continuous) at T_C = 25°C	120	A
I_D (1)	Drain current (continuous) at T_C=100°C	110	A
I_{DM} (2)	Drain current (pulsed)	480	A
P_{TOT}	Total dissipation at T_C = 25°C	315	W
	Derating factor	2.1	W/°C
dv/dt	Peak diode recovery voltage slope	20	V/ns
E_{AS} (3)	Single pulse avalanche energy	350	mJ
T_j T_{stg}	Operating junction temperature storage temperature	- 55 to 175	°C

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting Tj = 25 °C, I_D = 80 A, V_{DD} = 50 V.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case	0.48	°C/W
Rthj-a	Thermal resistance junction-ambient max	62.5	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage (V_{GS}= 0)	I_D = 250 µA	100			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS}= 100 V V_{DS}= 100 V, T_C= 125°C			10 100	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±20 V			±200	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10 V, I_D= 60 A		4.5	5.1	mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0	-	6665 786 49	-	pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 50 V, I_D = 120 A, V_{GS} = 10 V (see *Figure 14*)	-	114.6 38.8 31.9	-	nC nC nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 50 V, I_D = 60 A R_G = 4.7 Ω V_{GS} = 10 V (see *Figure 13*, *Figure 18*)	-	25.6 97.1 99.9 6.9	-	ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(1)	Source-drain current Source-drain current (pulsed)		-		120 480	A A
V_{SD}(2)	Forward on voltage	I_{SD}=120 A, V_{GS}=0	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=120 A, di/dt = 100 A/µs, V_{DD}=80 V, Tj=150°C (see *Figure 15*)	-	83.4 295.7 7.1		ns nC A

1. Pulse width limited by safe operating area.
2. Pulse duration = 300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

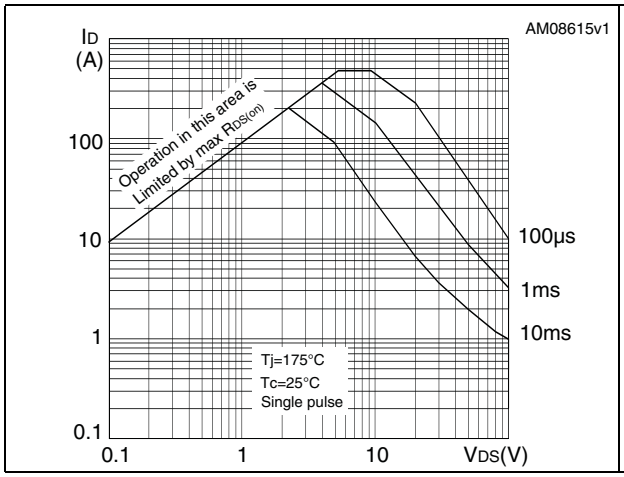


Figure 3. Thermal impedance

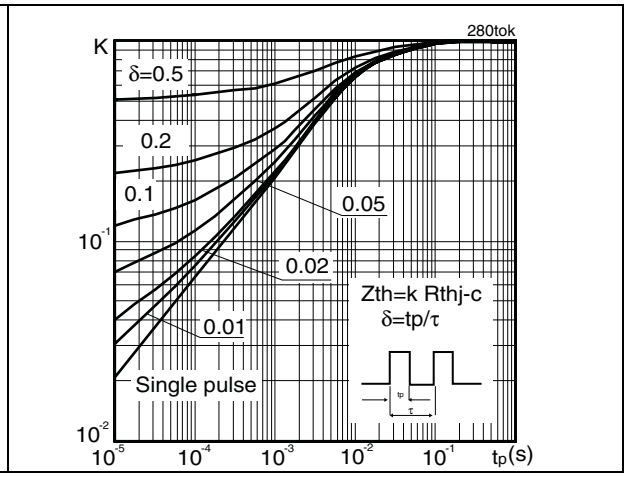


Figure 4. Output characteristics

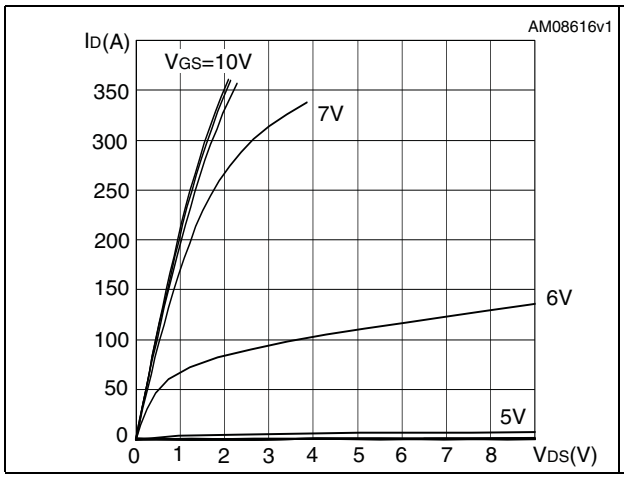


Figure 5. Transfer characteristics

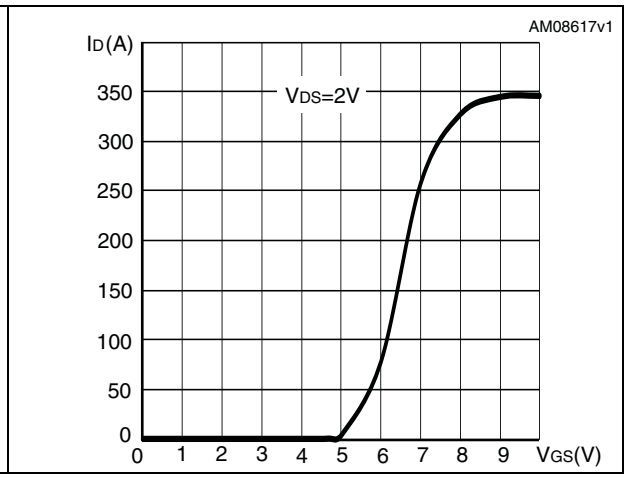


Figure 6. Static drain-source on resistance

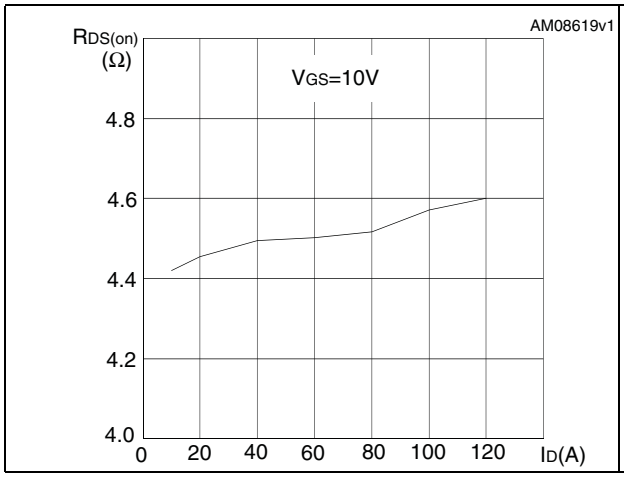


Figure 7. Source-drain diode forward characteristics

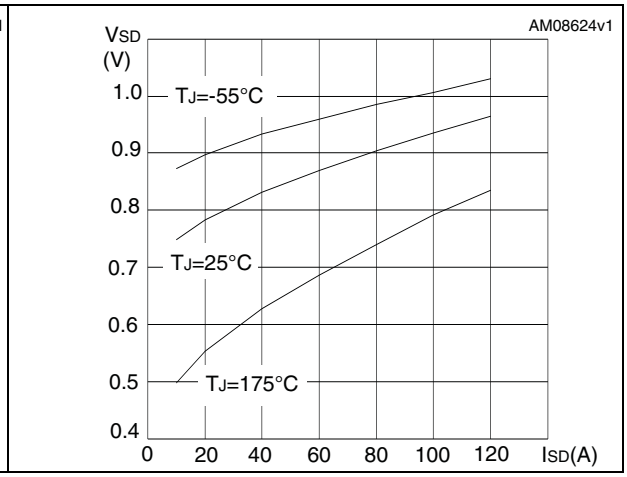


Figure 8. Gate charge vs gate-source voltage

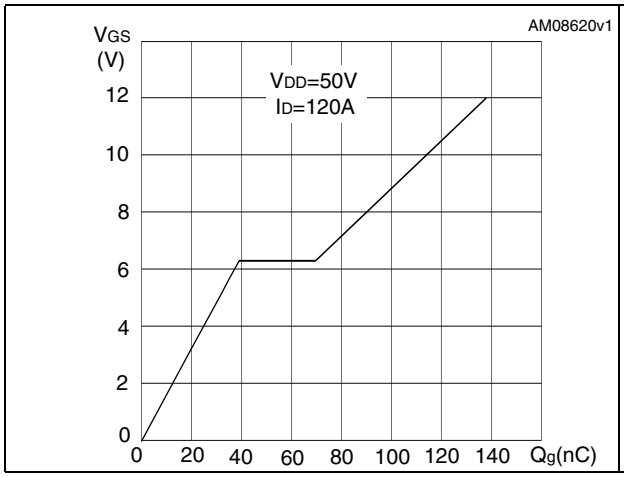


Figure 9. Capacitance variations

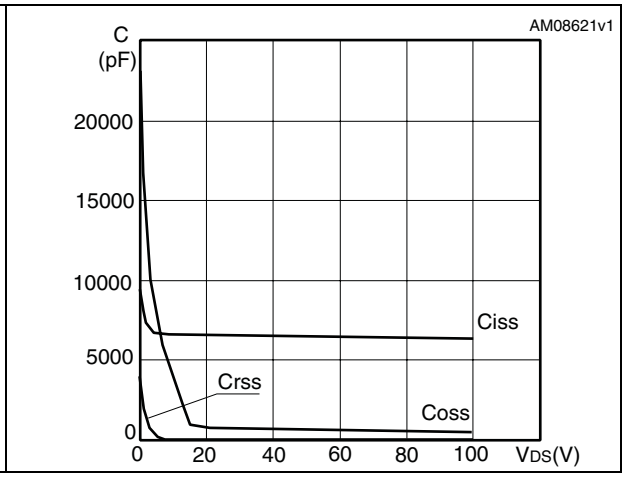


Figure 10. Normalized gate threshold voltage vs temperature

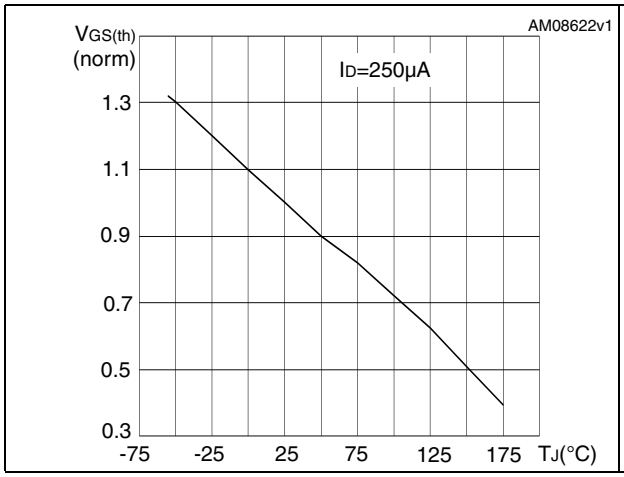


Figure 11. Normalized on resistance vs temperature

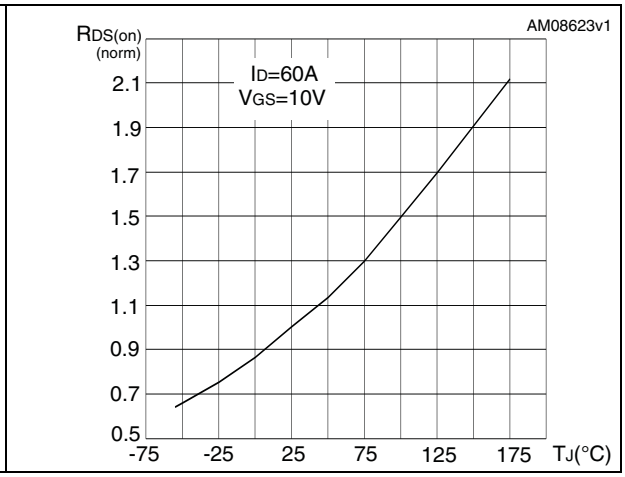
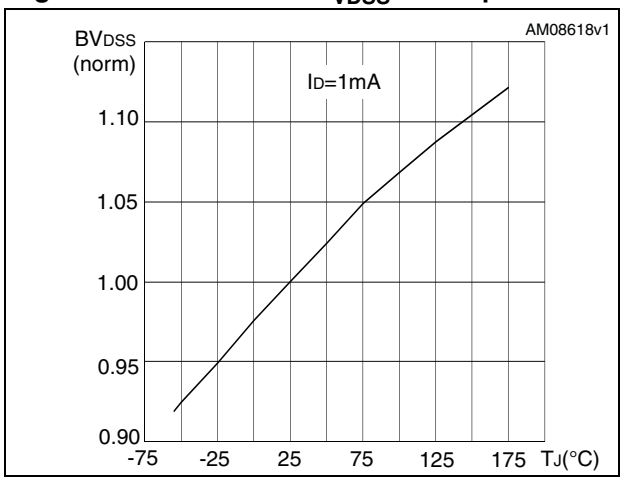


Figure 12. Normalized B_{VDSS} vs temperature



3 Test circuits

Figure 13. Switching times test circuit for resistive load

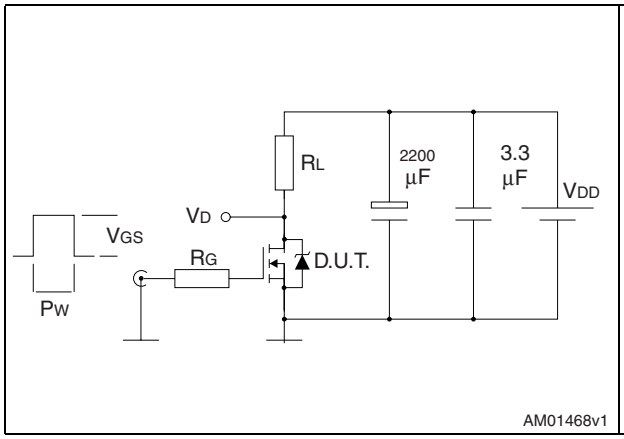


Figure 14. Gate charge test circuit

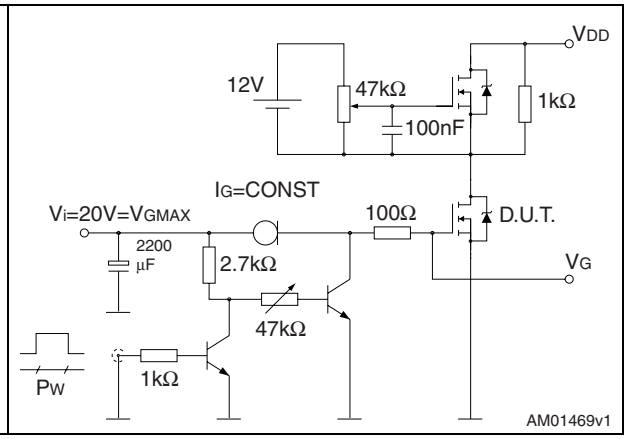


Figure 15. Test circuit for inductive load switching and diode recovery times

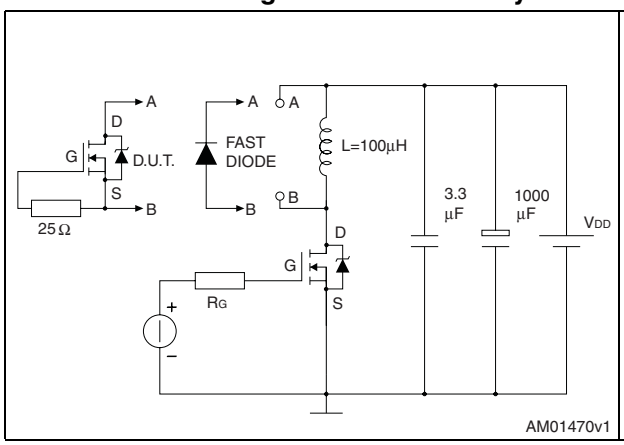


Figure 16. Unclamped inductive load test circuit

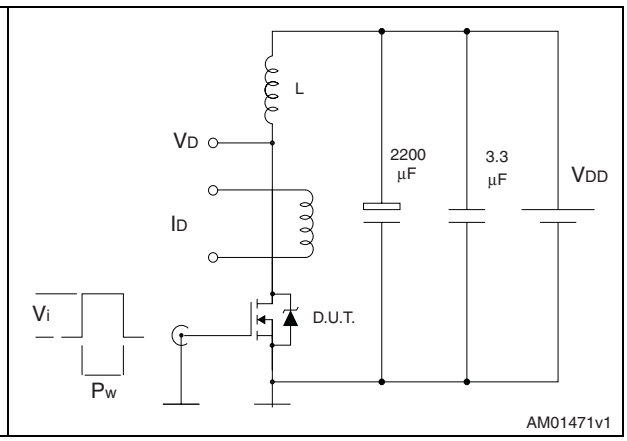


Figure 17. Unclamped inductive waveform

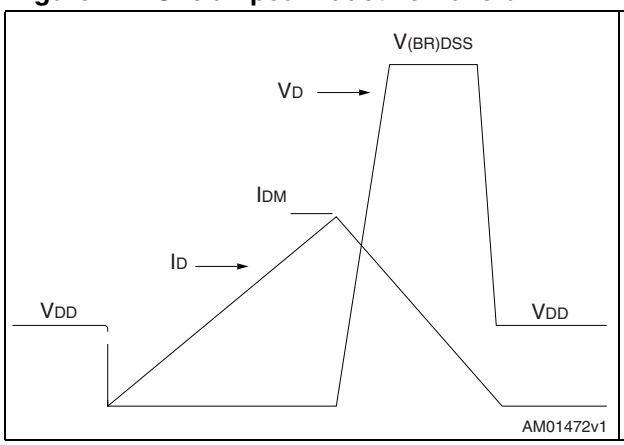
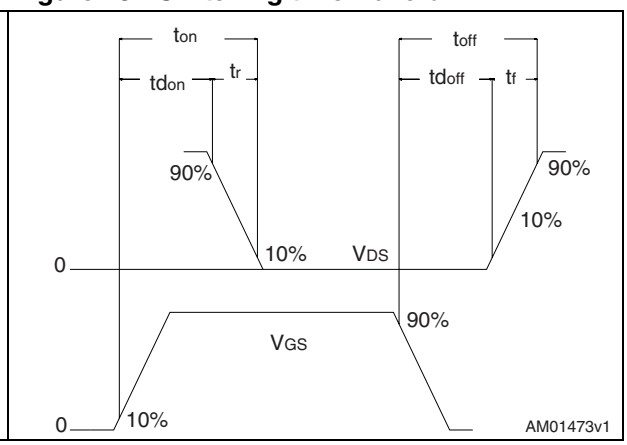


Figure 18. Switching time waveform



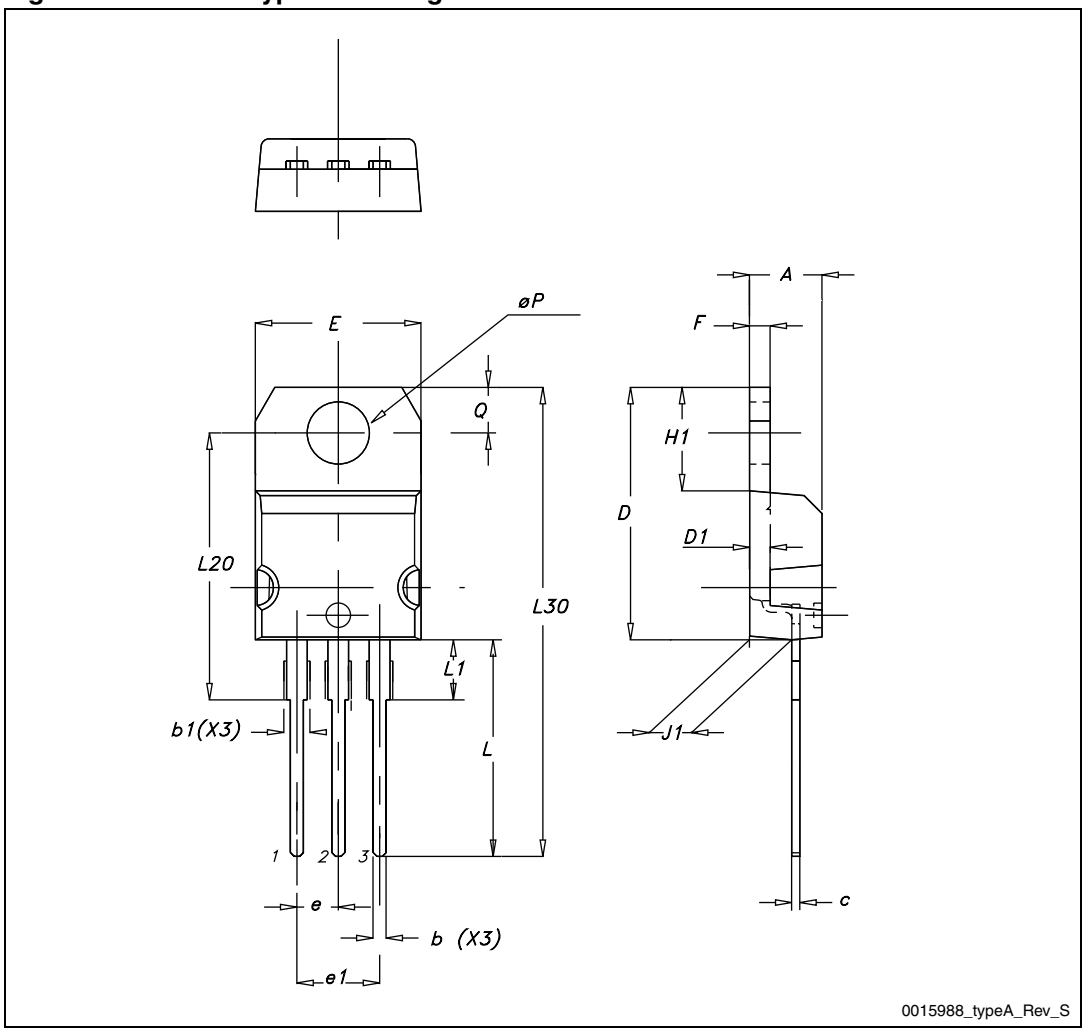
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
01-Aug-2008	1	First version
03-Jun-2010	2	– Removed package, mechanical data: D²PAK – Added new package mechanical data: H²PAK
10-Mar-2011	3	Document status promoted from preliminary data to datasheet.
11-Jul-2011	4	Removed part number in H²PAK.

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